



EIC8596-2

UPDATED 07/25/2007

8.50-9.60 GHz 2-Watt Internally-Matched Power FET

FEATURES

- 8.50-9.60GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +33.5 dBm Output Power at 1dB Compression
- 8.0 dB Power Gain at 1dB Compression
- 30% Power Added Efficiency
- -46 dBc IM3 at PO = 22.5 dBm SCL
- 100% Tested for DC, RF, and R_{TH}

ELECTRICAL CHARACTERISTICS (T_a = 25°C)

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
P_{1dB}	Output Power at 1dB Compression V _{DS} = 10 V, I _{DSQ} ≈ 550mA	32.5	33.5		dBm
G_{1dB}	Gain at 1dB Compression V _{DS} = 10 V, I _{DSQ} ≈ 550mA	7.0	8.0		dB
ΔG	Gain Flatness V _{DS} = 10 V, I _{DSQ} ≈ 550mA		±0.6	+ 0.8	dB
PAE	Power Added Efficiency at 1dB Compression V _{DS} = 10 V, I _{DSQ} ≈ 550mA		30		%
I_{d1dB}	Drain Current at 1dB Compression f = 8.50-9.60GHz		600	700	mA
IM3	Output 3rd Order Intermodulation Distortion Δf = 10 MHz 2-Tone Test; Pout = 22.5 dBm S.C.L. ² V _{DS} = 10 V, I _{DSQ} ≈ 65% IDSS	-43	-46		dBc
I_{DSS}	Saturated Drain Current V _{DS} = 3 V, V _{GS} = 0 V		1000	1250	mA
V_P	Pinch-off Voltage V _{DS} = 3 V, I _{DS} = 10 mA		-2.5	-4.0	V
R_{TH}	Thermal Resistance ³		11	12	°C/W

Notes:

1. Tested with 100 Ohm gate resistor.
2. S.C.L. = Single Carrier Level.
3. Overall R_{th} depends on case mounting.

MAXIMUM RATING AT 25 °C^{1,2}

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²
V_{ds}	Drain-Source Voltage	15	10V
V_{gs}	Gate-Source Voltage	-5	-4V
I_{gsf}	Forward Gate Current	21.6mA	7.2mA
I_{gsr}	Reverse Gate Current	-3.6mA	-1.2mA
P_{in}	Input Power	32.5dBm	@ 3dB Compression
T_{ch}	Channel Temperature	175 °C	175 °C
T_{stg}	Storage Temperature	-65 to +175 °C	-65 to +175 °C
P_t	Total Power Dissipation	12.5W	12.5W

- Note: 1. Exceeding any of the above ratings may result in permanent damage.
2. Exceeding any of the above ratings may reduce MTTF below design goals.

Specifications are subject to change without notice.

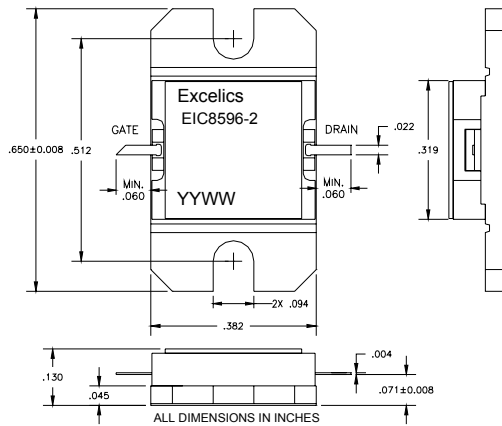
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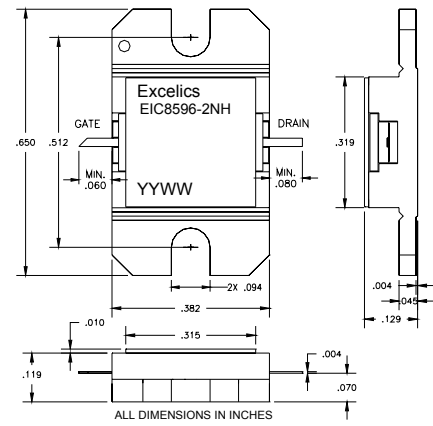
PACKAGES OUTLINE

Dimensions in inches, Tolerance $\pm .005$ unless otherwise specified

EIC8596-2 (Hermetic)



EIC8596-2NH (Non-Hermetic)



Caution! ESD sensitive device.



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ORDERING INFORMATION

Part Number	Packages	Grade ¹	f _{Test} (GHz)	P _{1dB} (min)	IM ₃ (min) ²
EIC8596-2	Hermetic	Industrial	8.50-9.60GHz	32.5	-43
EIC8596-2NH	Non-Hermetic	Industrial	8.50-9.60GHz	32.5	-43

Notes: 1. Contact factory for military and hi-rel grades.
2. Exact test conditions are specified in "Electrical Characteristics" table.

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